

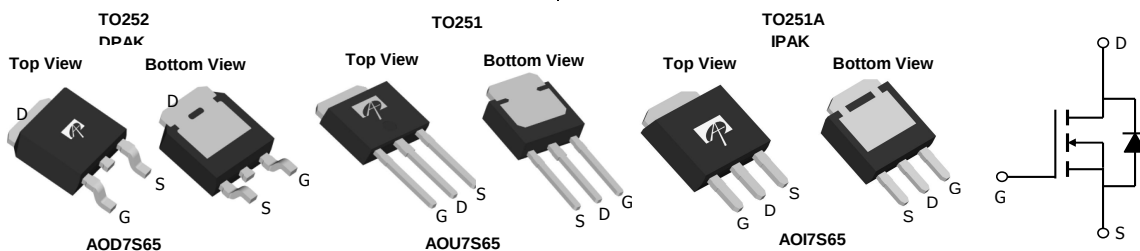
### General Description

The AOD7S65 & AOU7S65 & AOI7S65 have been fabricated using the advanced  $\alpha$ MOS™ high voltage process that is designed to deliver high levels of performance and robustness in switching applications. By providing low  $R_{DS(on)}$ ,  $Q_g$  and  $E_{OSS}$  along with guaranteed avalanche capability these parts can be adopted quickly into new and existing offline power supply designs.

### Product Summary

|                      |               |
|----------------------|---------------|
| $V_{DS} @ T_{j,max}$ | 750V          |
| $I_{DM}$             | 30A           |
| $R_{DS(ON),max}$     | 0.65 $\Omega$ |
| $Q_{g,typ}$          | 9.2nC         |
| $E_{OSS} @ 400V$     | 2 $\mu$ J     |

100% UIS Tested  
 100%  $R_g$  Tested



### Absolute Maximum Ratings $T_A=25^\circ\text{C}$ unless otherwise noted

| Parameter                                                                                 | Symbol         | Maximum    | Units |
|-------------------------------------------------------------------------------------------|----------------|------------|-------|
| Drain-Source Voltage                                                                      | $V_{DS}$       | 650        | V     |
| Gate-Source Voltage                                                                       | $V_{GS}$       | $\pm 30$   | V     |
| Continuous Drain Current                                                                  | $I_D$          | 7          | A     |
| $T_C=25^\circ\text{C}$                                                                    |                | 5          |       |
| Pulsed Drain Current <sup>C</sup>                                                         | $I_{DM}$       | 30         | A     |
| Avalanche Current <sup>C</sup>                                                            | $I_{AR}$       | 1.7        | A     |
| Repetitive avalanche energy <sup>C</sup>                                                  | $E_{AR}$       | 43         | mJ    |
| Single pulsed avalanche energy <sup>H</sup>                                               | $E_{AS}$       | 86         | mJ    |
| Power Dissipation <sup>B</sup>                                                            | $P_D$          | 89         | W     |
| $T_C=25^\circ\text{C}$                                                                    |                | 0.7        | W/°C  |
| Derate above 25°C                                                                         |                |            |       |
| MOSFET dv/dt ruggedness                                                                   | dv/dt          | 100        | V/ns  |
| Peak diode recovery dv/dt                                                                 |                | 20         |       |
| Junction and Storage Temperature Range                                                    | $T_J, T_{STG}$ | -55 to 150 | °C    |
| Maximum lead temperature for soldering purpose, 1/8" from case for 5 seconds <sup>K</sup> | $T_L$          | 300        | °C    |

### Thermal Characteristics

| Parameter                                  | Symbol          | Typical | Maximum | Units |
|--------------------------------------------|-----------------|---------|---------|-------|
| Maximum Junction-to-Ambient <sup>A,D</sup> | $R_{\theta JA}$ | 45      | 55      | °C/W  |
| Maximum Case-to-sink <sup>A</sup>          | $R_{\theta CS}$ | --      | 0.5     | °C/W  |
| Maximum Junction-to-Case <sup>D,F</sup>    | $R_{\theta JC}$ | 1.1     | 1.4     | °C/W  |

**Electrical Characteristics (T<sub>J</sub>=25°C unless otherwise noted)**

| Symbol                      | Parameter                                                 | Conditions                                                                             | Min | Typ  | Max  | Units |
|-----------------------------|-----------------------------------------------------------|----------------------------------------------------------------------------------------|-----|------|------|-------|
| <b>STATIC PARAMETERS</b>    |                                                           |                                                                                        |     |      |      |       |
| BV <sub>DSS</sub>           | Drain-Source Breakdown Voltage                            | I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C                       | 650 | -    | -    | V     |
|                             |                                                           | I <sub>D</sub> =250μA, V <sub>GS</sub> =0V, T <sub>J</sub> =150°C                      | 700 | 750  | -    |       |
| I <sub>DSS</sub>            | Zero Gate Voltage Drain Current                           | V <sub>DS</sub> =650V, V <sub>GS</sub> =0V                                             | -   | -    | 1    | μA    |
|                             |                                                           | V <sub>DS</sub> =520V, T <sub>J</sub> =150°C                                           | -   | 10   | -    |       |
| I <sub>GSS</sub>            | Gate-Body leakage current                                 | V <sub>DS</sub> =0V, V <sub>GS</sub> =±30V                                             | -   | -    | ±100 | nA    |
| V <sub>GS(th)</sub>         | Gate Threshold Voltage                                    | V <sub>DS</sub> =5V, I <sub>D</sub> =250μA                                             | 2.6 | 3.3  | 4    | V     |
| R <sub>DS(ON)</sub>         | Static Drain-Source On-Resistance                         | V <sub>GS</sub> =10V, I <sub>D</sub> =3.5A, T <sub>J</sub> =25°C                       | -   | 0.54 | 0.65 | Ω     |
|                             |                                                           | V <sub>GS</sub> =10V, I <sub>D</sub> =3.5A, T <sub>J</sub> =150°C                      | -   | 1.48 | 1.64 | Ω     |
| V <sub>SD</sub>             | Diode Forward Voltage                                     | I <sub>S</sub> =3.5A, V <sub>GS</sub> =0V, T <sub>J</sub> =25°C                        | -   | 0.82 | -    | V     |
| I <sub>S</sub>              | Maximum Body-Diode Continuous Current                     |                                                                                        | -   | -    | 7    | A     |
| I <sub>SM</sub>             | Maximum Body-Diode Pulsed Current <sup>C</sup>            |                                                                                        | -   | -    | 30   | A     |
| <b>DYNAMIC PARAMETERS</b>   |                                                           |                                                                                        |     |      |      |       |
| C <sub>iss</sub>            | Input Capacitance                                         | V <sub>GS</sub> =0V, V <sub>DS</sub> =100V, f=1MHz                                     | -   | 434  | -    | pF    |
| C <sub>oss</sub>            | Output Capacitance                                        |                                                                                        | -   | 30   | -    | pF    |
| C <sub>o(er)</sub>          | Effective output capacitance, energy related <sup>I</sup> | V <sub>GS</sub> =0V, V <sub>DS</sub> =0 to 480V, f=1MHz                                | -   | 23   | -    | pF    |
| C <sub>o(tr)</sub>          | Effective output capacitance, time related <sup>J</sup>   |                                                                                        | -   | 80   | -    | pF    |
| C <sub>rss</sub>            | Reverse Transfer Capacitance                              | V <sub>GS</sub> =0V, V <sub>DS</sub> =100V, f=1MHz                                     | -   | 1    | -    | pF    |
| R <sub>g</sub>              | Gate resistance                                           | V <sub>GS</sub> =0V, V <sub>DS</sub> =0V, f=1MHz                                       | -   | 17.5 | -    | Ω     |
| <b>SWITCHING PARAMETERS</b> |                                                           |                                                                                        |     |      |      |       |
| Q <sub>g</sub>              | Total Gate Charge                                         | V <sub>GS</sub> =10V, V <sub>DS</sub> =480V, I <sub>D</sub> =3.5A                      | -   | 9.2  | -    | nC    |
| Q <sub>gs</sub>             | Gate Source Charge                                        |                                                                                        | -   | 2.5  | -    | nC    |
| Q <sub>gd</sub>             | Gate Drain Charge                                         |                                                                                        | -   | 2.7  | -    | nC    |
| t <sub>D(on)</sub>          | Turn-On DelayTime                                         | V <sub>GS</sub> =10V, V <sub>DS</sub> =400V, I <sub>D</sub> =3.5A, R <sub>G</sub> =25Ω | -   | 21   | -    | ns    |
| t <sub>r</sub>              | Turn-On Rise Time                                         |                                                                                        | -   | 14   | -    | ns    |
| t <sub>D(off)</sub>         | Turn-Off DelayTime                                        |                                                                                        | -   | 55   | -    | ns    |
| t <sub>f</sub>              | Turn-Off Fall Time                                        |                                                                                        | -   | 15   | -    | ns    |
| t <sub>rr</sub>             | Body Diode Reverse Recovery Time                          | I <sub>F</sub> =3.5A, dI/dt=100A/μs, V <sub>DS</sub> =400V                             | -   | 224  | -    | ns    |
| I <sub>rm</sub>             | Peak Reverse Recovery Current                             | I <sub>F</sub> =3.5A, dI/dt=100A/μs, V <sub>DS</sub> =400V                             | -   | 19   | -    | A     |
| Q <sub>rr</sub>             | Body Diode Reverse Recovery Charge                        | I <sub>F</sub> =3.5A, dI/dt=100A/μs, V <sub>DS</sub> =400V                             | -   | 2.8  | -    | μC    |

A. The value of R<sub>θJA</sub> is measured with the device in a still air environment with T<sub>A</sub>=25°C.

B. The power dissipation P<sub>D</sub> is based on T<sub>J(MAX)</sub>=150°C, using junction-to-case thermal resistance, and is more useful in setting the upper dissipation limit for cases where additional heatsinking is used.

C. Repetitive rating, pulse width limited by junction temperature T<sub>J(MAX)</sub>=150°C. Ratings are based on low frequency and duty cycles to keep initial T<sub>J</sub>=25°C.

D. The R<sub>θJA</sub> is the sum of the thermal impedance from junction to case R<sub>θJC</sub> and case to ambient.

E. The static characteristics in Figures 1 to 6 are obtained using <300 μs pulses, duty cycle 0.5% max.

F. These curves are based on the junction-to-case thermal impedance which is measured with the device mounted to a large heatsink, assuming a maximum junction temperature of T<sub>J(MAX)</sub>=150°C. The SOA curve provides a single pulse rating.

G. These tests are performed with the device mounted on 1 in<sup>2</sup> FR-4 board with 2oz. Copper, in a still air environment with T<sub>A</sub>=25°C.

H. L=60mH, I<sub>AS</sub>=1.7A, V<sub>DD</sub>=150V, Starting T<sub>J</sub>=25°C

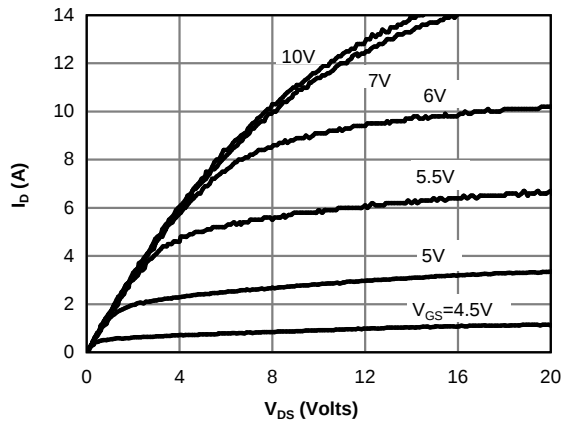
I. C<sub>o(er)</sub> is a fixed capacitance that gives the same stored energy as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>(BR)DSS</sub>.

J. C<sub>o(tr)</sub> is a fixed capacitance that gives the same charging time as C<sub>oss</sub> while V<sub>DS</sub> is rising from 0 to 80% V<sub>(BR)DSS</sub>.

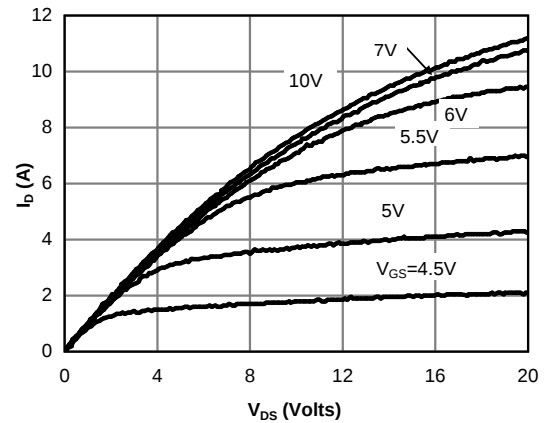
K. Wave soldering only allowed at leads.

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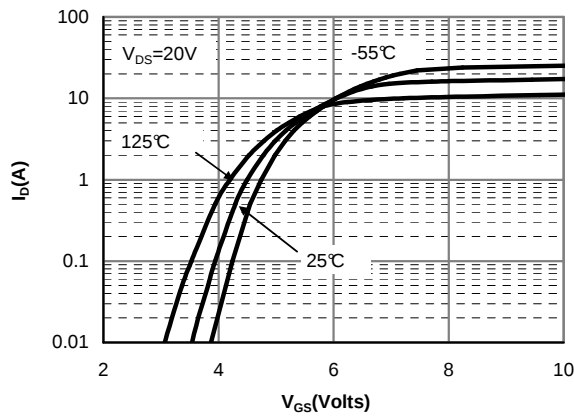
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



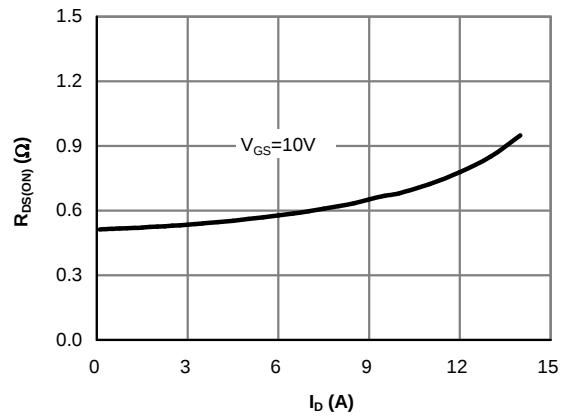
**Figure 1: On-Region Characteristics@25°C**



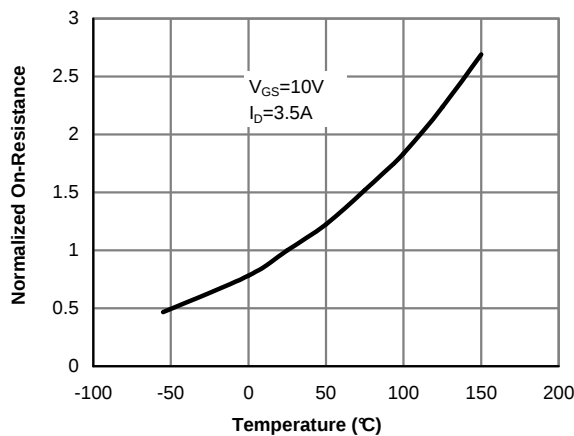
**Figure 2: On-Region Characteristics@125°C**



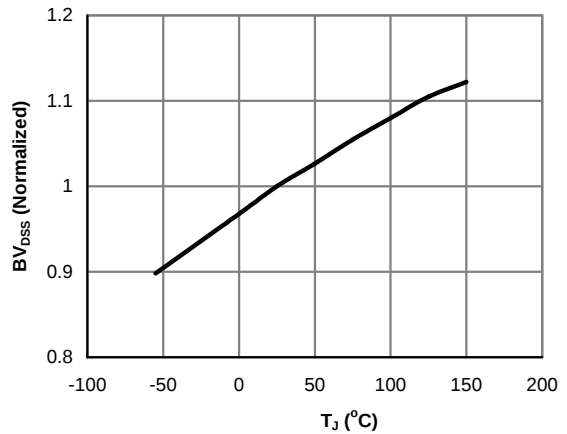
**Figure 3: Transfer Characteristics**



**Figure 4: On-Resistance vs. Drain Current and Gate Voltage**

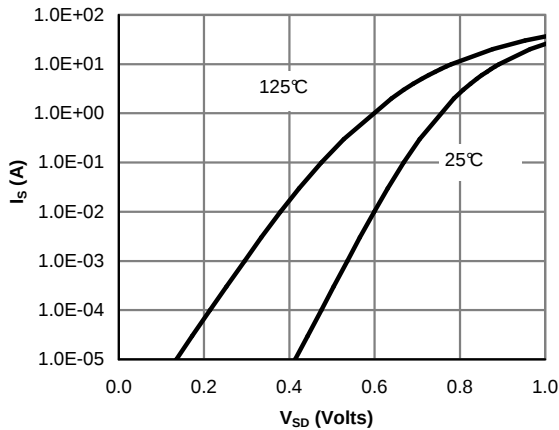


**Figure 5: On-Resistance vs. Junction Temperature**

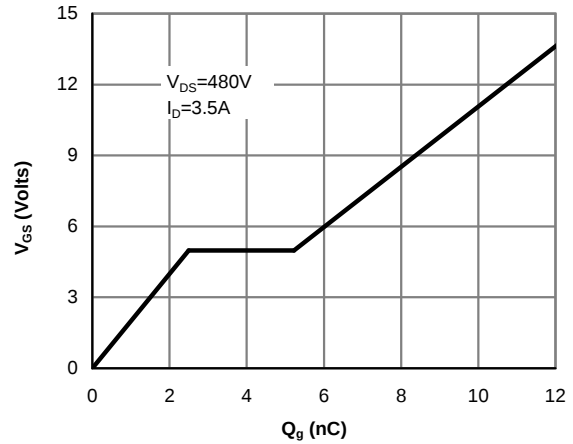


**Figure 6: Break Down vs. Junction Temperature**

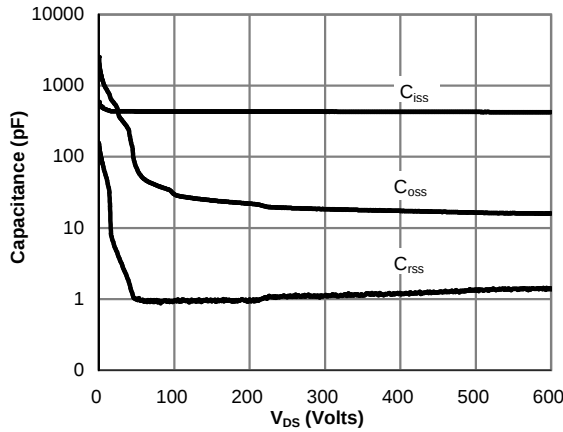
**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**



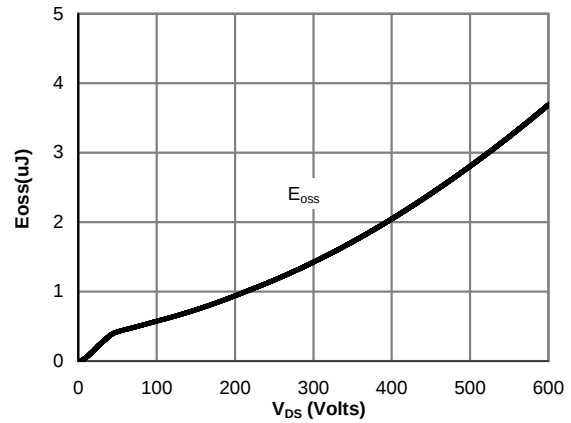
**Figure 7: Body-Diode Characteristics (Note E)**



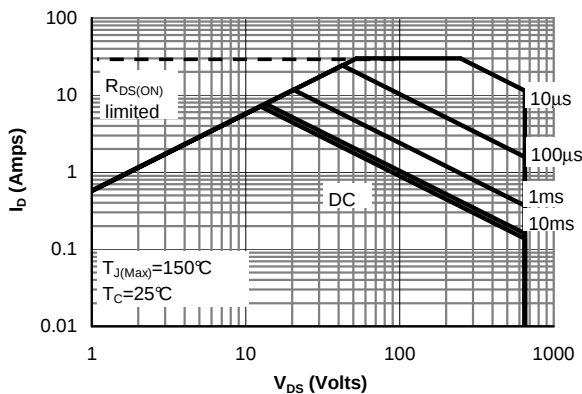
**Figure 8: Gate-Charge Characteristics**



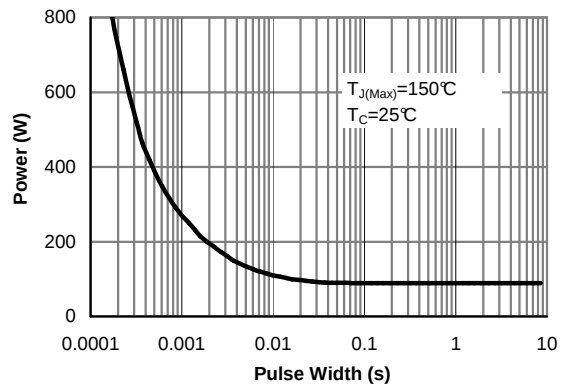
**Figure 9: Capacitance Characteristics**



**Figure 10: Coss stored Energy**



**Figure 11: Maximum Forward Biased Safe Operating Area (Note F)**



**Figure 12: Single Pulse Power Rating Junction-to-Case (Note F)**

# TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS

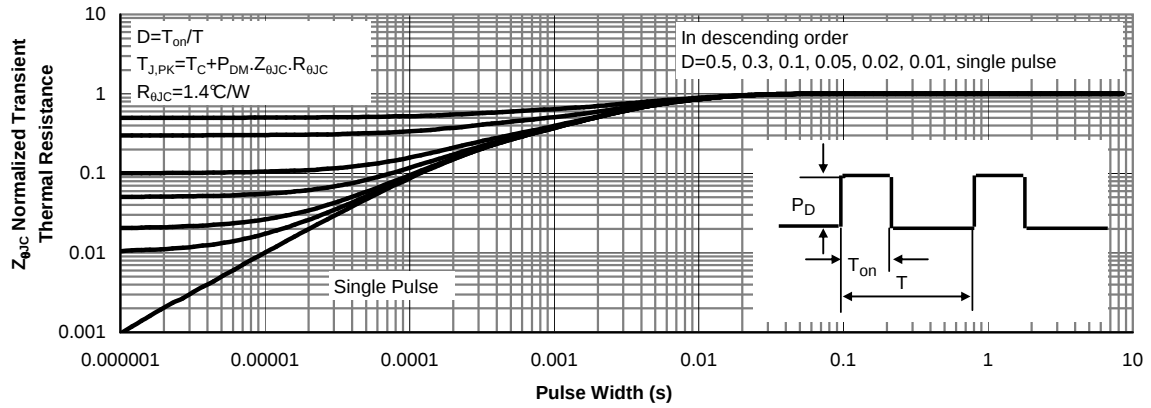


Figure 13: Normalized Maximum Transient Thermal Impedance (Note F)

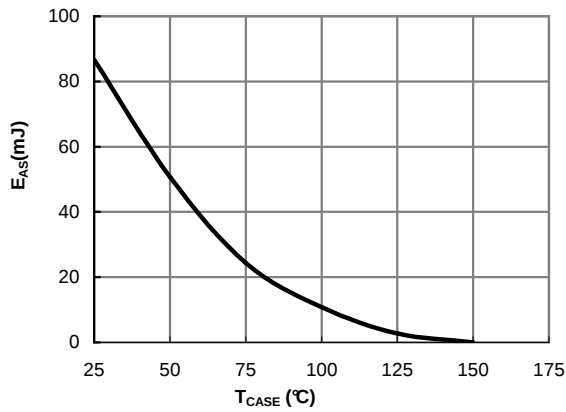


Figure 14: Avalanche energy

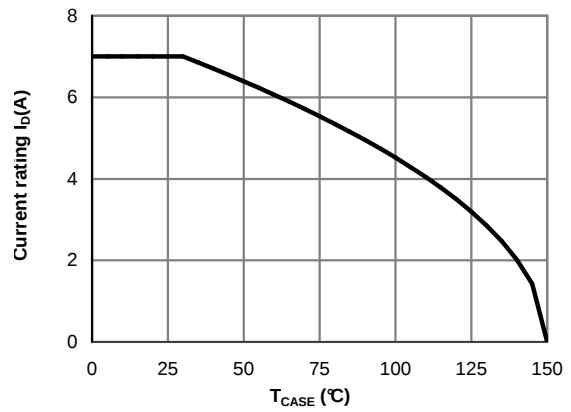


Figure 15: Current De-rating (Note B)

**TYPICAL ELECTRICAL AND THERMAL CHARACTERISTICS**

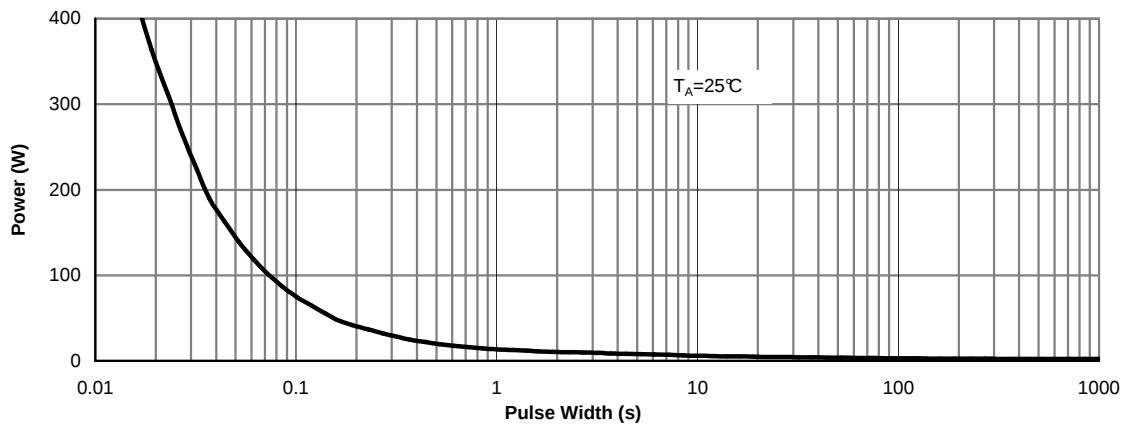


Figure 16: Single Pulse Power Rating Junction-to-Ambient (Note G)

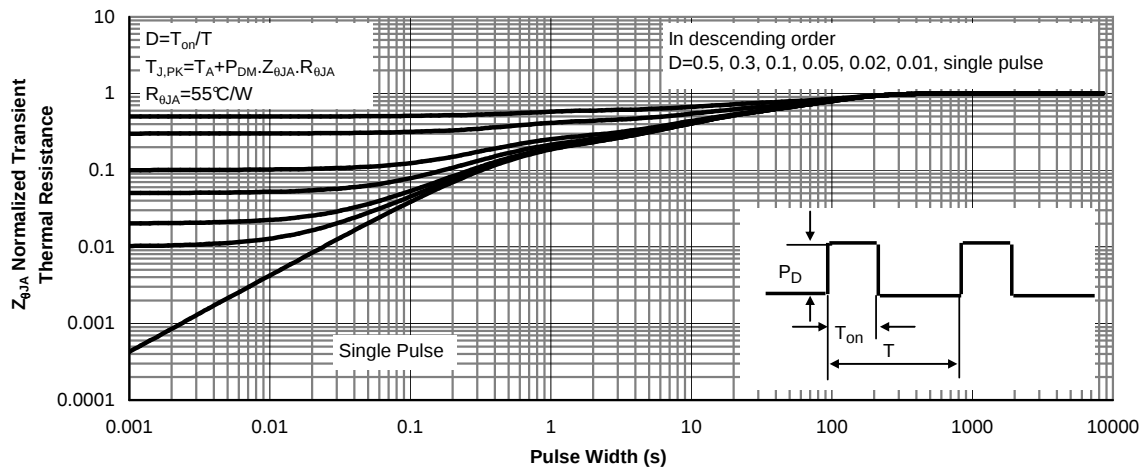
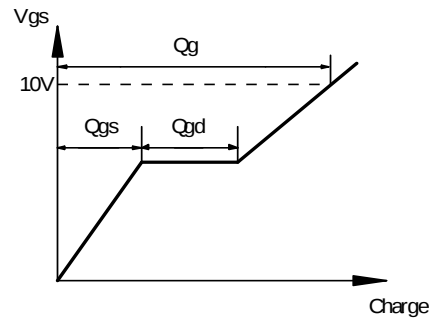
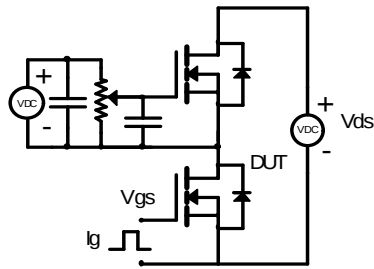
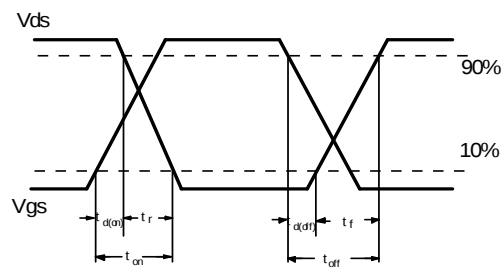
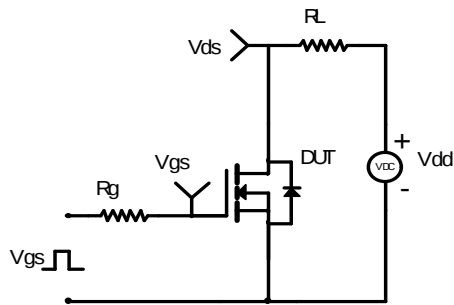


Figure 17: Normalized Maximum Transient Thermal Impedance (Note G)

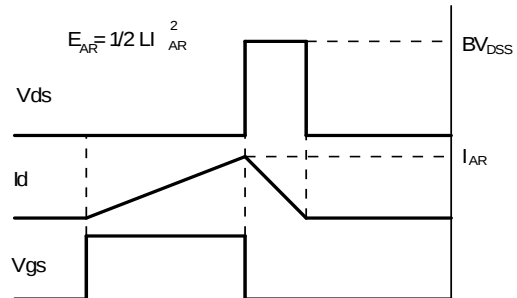
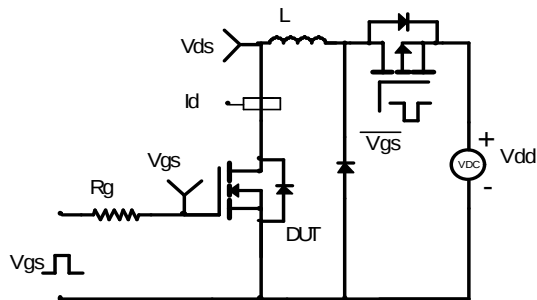
Gate Charge Test Circuit & Waveform



Resistive Switching Test Circuit & Waveforms



Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms

